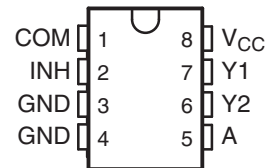


## SINGLE-POLE DOUBLE-THROW (SPDT) ANALOG SWITCH OR 2:1 ANALOG MULTIPLEXER/DEMULTIPLEXER

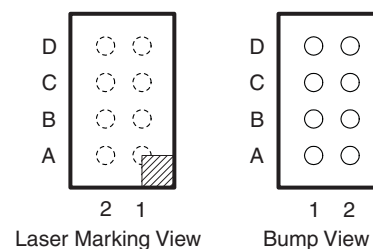
### FEATURES

- Available in the Texas Instruments NanoFree™ Package
- Operates at 0.8 V to 2.7 V
- Sub-1-V Operable
- Low Power Consumption, 10  $\mu$ A at 2.7 V
- High On-Off Output Voltage Ratio
- High Degree of Linearity
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
  - 2000-V Human-Body Model (A114-A)
  - 200-V Machine Model (A115-A)
  - 1000-V Charged-Device Model (C101)

DCT OR DCU PACKAGE  
(TOP VIEW)



YZP PACKAGE



### YZP TERMINAL ASSIGNMENTS

<b>D</b>	GND	A
<b>C</b>	GND	Y2
<b>B</b>	INH	Y1
<b>A</b>	COM	V <sub>CC</sub>
	1	2

### DESCRIPTION/ORDERING INFORMATION

This analog switch is operational at 0.8-V to 2.7-V V<sub>CC</sub>, but is designed specifically for 1.1-V to 2.7-V V<sub>CC</sub> operation.

The SN74AUC2G53 can handle both analog and digital signals. The device permits signals with amplitudes of up to V<sub>CC</sub> (peak) to be transmitted in either direction.

NanoFree™ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

Applications include signal gating, chopping, modulation or demodulation (modem), and signal multiplexing for analog-to-digital and digital-to-analog conversion systems.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

NanoFree is a trademark of Texas Instruments.

**ORDERING INFORMATION**

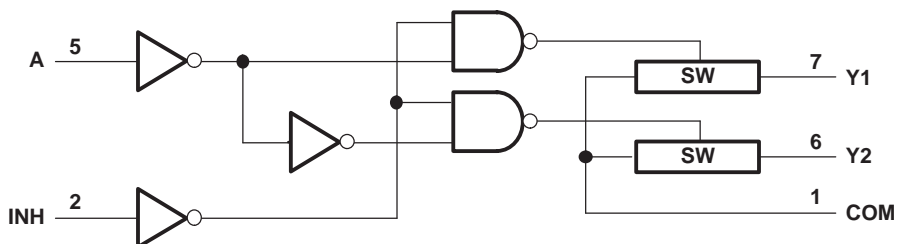
T <sub>A</sub>	PACKAGE <sup>(1)(2)</sup>		ORDERABLE PART NUMBER	TOP-SIDE MARKING <sup>(3)</sup>
-40C to 85C	NanoFree™ – WCSP (DSBGA) 0.23-mm Large Bump – YZP (Pb-free)	Reel of 3000	SN74AUC2G53YZPR	___U4_
	SSOP – DCT	Reel of 3000	SN74AUC2G53DCTR	U53___
	VSSOP – DCU	Reel of 3000	SN74AUC2G53DCUR	U53_

- (1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at [www.ti.com](http://www.ti.com).
- (2) Package drawings, thermal data, and symbolization are available at [www.ti.com/packaging](http://www.ti.com/packaging).
- (3) DCT: The actual top-side marking has three additional characters that designate the year, month, and assembly/test site.  
DCU: The actual top-side marking has one additional character that designates the assembly/test site.  
YZP: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the assembly/test site. Pin 1 identifier indicates solder-bump composition (1 = SnPb, • = Pb-free).

**FUNCTION TABLE**

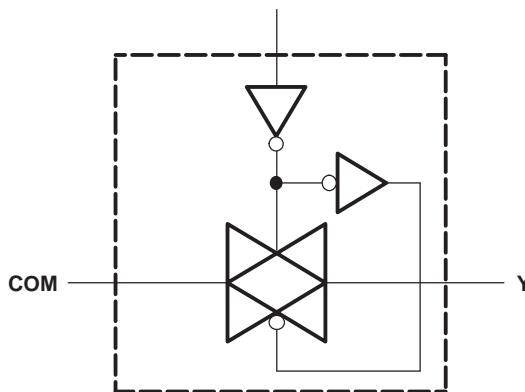
CONTROL INPUTS		ON CHANNEL
INH	A	
L	L	Y1
L	H	Y2
H	X	None

**LOGIC DIAGRAM (POSITIVE LOGIC)**



NOTE A: For simplicity, the test conditions shown in Figures 1 through 4 and 6 through 10 are for the demultiplexer configuration. Signals may be passed from COM to Y1 (Y2) or from Y1 (Y2) to COM.

**SIMPLIFIED SCHEMATIC, EACH SWITCH (SW)**



## Absolute Maximum Ratings<sup>(1)</sup>

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage range <sup>(2)</sup>	–0.5	3.6	V
V <sub>I</sub>	Input voltage range <sup>(2)(3)</sup>	–0.5	3.6	V
V <sub>I/O</sub>	Switch I/O voltage range <sup>(2)(3)</sup>	–0.5	V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	Control input clamp current	V <sub>I</sub> < 0	–50	mA
I <sub>I/O</sub> K	I/O port diode current	V <sub>I/O</sub> < 0 or V <sub>I/O</sub> > V <sub>CC</sub>	50	mA
I <sub>T</sub>	On-state switch current	V <sub>I/O</sub> = 0 to V <sub>CC</sub>	50	mA
	Continuous current through V <sub>CC</sub> or GND		100	mA
θ <sub>JA</sub>	Package thermal impedance <sup>(4)</sup>	DCT package	220	C/W
		DCU package	227	
		YZP package	102	
T <sub>stg</sub>	Storage temperature range	–65	150	C

- (1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltages are with respect to ground unless otherwise specified.
- (3) The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
- (4) The package thermal impedance is calculated in accordance with JESD 51-7.

## Recommended Operating Conditions<sup>(1)</sup>

		MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage	0.8	2.7	V
V <sub>IH</sub>	High-level input voltage	V <sub>CC</sub> = 0.8 V	V <sub>CC</sub>	V
		V <sub>CC</sub> = 1.1 V to 1.95 V	0.65 V <sub>CC</sub>	
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.7	
V <sub>IL</sub>	Low-level input voltage	V <sub>CC</sub> = 0.8 V	0	V
		V <sub>CC</sub> = 1.1 V to 1.95 V	0.35 V <sub>CC</sub>	
		V <sub>CC</sub> = 2.3 V to 2.7 V	0.7	
V <sub>I/O</sub>	I/O port voltage	0	V <sub>CC</sub>	V
V <sub>I</sub>	Control input voltage	0	3.6	V
Δt/Δv	Input transition rise or fall rate	V <sub>CC</sub> = 0.8 V to 1.6 V	20	ns/V
		V <sub>CC</sub> = 1.65 V to 1.95 V	10	
		V <sub>CC</sub> = 2.3 V to 2.7 V	3.5	
T <sub>A</sub>	Operating free-air temperature	–40	85	C

- (1) All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

## Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V <sub>CC</sub>	MIN	TYP <sup>(1)</sup>	MAX	UNIT
r <sub>on</sub>	On-state switch resistance V <sub>I</sub> = V <sub>CC</sub> or GND, V <sub>INH</sub> = V <sub>IL</sub> (see Figure 1 and Figure 2)	I <sub>S</sub> = 4 mA	1.1 V		40	Ω
			1.65 V	12.5	20	
		I <sub>S</sub> = 8 mA	2.3 V	6	15	
r <sub>on(p)</sub>	Peak on resistance V <sub>I</sub> = V <sub>CC</sub> to GND, V <sub>INH</sub> = V <sub>IL</sub> (see Figure 1 and Figure 2)	I <sub>S</sub> = 4 mA	1.1 V	131	180	Ω
			1.65 V	32	80	
		I <sub>S</sub> = 8 mA	2.3 V	15	20	

- (1) T<sub>A</sub> = 25°C

## Electrical Characteristics (continued)

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V <sub>CC</sub>	MIN	TYP <sup>(1)</sup>	MAX	UNIT
$\Delta R_{on}$	Difference of on-state resistance between switches	$V_I = V_{CC}$ to GND, $V_C = V_{IH}$ (see Figure 1 and Figure 2)	$I_S = 4$ mA	1.1 V			4	$\Omega$
				1.65 V			1	
			$I_S = 8$ mA	2.3 V			1	
$I_{S(off)}$	Off-state switch leakage current	$V_I = V_{CC}$ and $V_O =$ GND, or $V_I =$ GND and $V_O = V_{CC}$ , $V_{INH} = V_{IH}$ (see Figure 3)		2.7 V			1	$\mu$ A
						0.1 <sup>(1)</sup>		
$I_{S(on)}$	On-state switch leakage current	$V_I = V_{CC}$ or GND, $V_{INH} = V_{IL}$ , $V_O =$ Open (see Figure 4)		2.7 V			1	$\mu$ A
						0.1 <sup>(1)</sup>		
$I_I$	Control input current	$V_C = V_{CC}$ or GND		2.7 V			5	$\mu$ A
$I_{CC}$	Supply current	$V_C = V_{CC}$ or GND		2.7 V			10	$\mu$ A
$C_{ic}$	Control input capacitance			2.5 V		2		pF
$C_{io(off)}$	Switch input/output capacitance	Y		2.5 V		3		pF
		COM			4.5			
$C_{io(on)}$	Switch input/output capacitance			2.5 V		9		pF

## Switching Characteristics

over recommended operating free-air temperature range,  $C_L = 15$  pF (unless otherwise noted) (see Figure 5)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub> = 0.8 V	V <sub>CC</sub> = 1.2 V 0.1 V		V <sub>CC</sub> = 1.5 V 0.1 V		V <sub>CC</sub> = 1.8 V 0.15 V			V <sub>CC</sub> = 2.5 V 0.2 V		UNIT
			TYP	MIN	MAX	MIN	MAX	MIN	TYP	MAX	MIN	MAX	
$t_{pd}^{(1)}$	COM or Y	Y or COM	0.3		0.3					0.2		0.1	ns
$t_{en}$	INH	COM or Y	9.2	0.5	3.5	0.5	2.2	0.5	1	1.9	0.5	1.8	ns
$t_{dis}$			8.1	0.5	4.2	0.5	3.2	0.5	1.9	3.4	0.5	2.6	
$t_{en}$	A	COM or Y	9.2	0.5	3.6	0.5	2.3	0.5	1.1	1.9	0.5	1.6	ns
$t_{dis}$			10	0.5	3.6	0.5	2.3	0.5	1.1	2	0.5	1.6	

(1) The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

## Switching Characteristics

over recommended operating free-air temperature range,  $C_L = 30$  pF (unless otherwise noted) (see Figure 5)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub> = 1.8 V 0.15 V			V <sub>CC</sub> = 2.5 V 0.2 V		UNIT
			MIN	TYP	MAX	MIN	MAX	
$t_{pd}^{(1)}$	COM or Y	Y or COM				0.4	0.2	ns
$t_{en}$	INH	COM or Y	0.5	1.6	3.1	0.5	2.2	ns
$t_{dis}$			0.5	2.2	3.4	0.5	2.2	
$t_{en}$	A	COM or Y	0.5	1.6	3	0.5	2.2	ns
$t_{dis}$			0.5	1.6	3	0.5	2.3	

(1) The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

## Analog Switch Characteristics

 $T_A = 25^\circ\text{C}$ 

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	V <sub>CC</sub>	TYP	UNIT
Frequency response <sup>(1)</sup> (switch ON)	COM or Y	Y or COM	$C_L = 50\text{ pF}$ , $R_L = 600\ \Omega$ , $f_{in} = \text{sine wave}$ (see Figure 6)	0.8 V	90	MHz
				1.1 V	101	
				1.4 V	110	
				1.65 V	122	
				2.3 V	198	
			$C_L = 5\text{ pF}$ , $R_L = 50\ \Omega$ , $f_{in} = \text{sine wave}$ (see Figure 6)	0.8 V	>500	
				1.1 V	>500	
				1.4 V	>500	
				1.65 V	>500	
				2.3 V	>500	
Crosstalk <sup>(2)</sup> (between switches)	COM or Y	Y or COM	$C_L = 50\text{ pF}$ , $R_L = 600\ \Omega$ , $f_{in} = 1\text{ MHz (sine wave)}$ (see Figure 7)	0.8 V	–59	dB
				1.1 V	–59	
				1.4 V	–59	
				1.65 V	–59	
				2.3 V	–60	
			$C_L = 5\text{ pF}$ , $R_L = 50\ \Omega$ , $f_{in} = 1\text{ MHz (sine wave)}$ (see Figure 7)	0.8 V	–55	
				1.1 V	–55	
				1.4 V	–55	
				1.65 V	–55	
				2.3 V	–55	
Crosstalk (control input to signal output)	INH	COM or Y	$C_L = 50\text{ pF}$ , $R_L = 600\ \Omega$ , $f_{in} = 1\text{ MHz (square wave)}$ (see Figure 8)	0.8 V	0.56	mV
				1.1 V	0.68	
				1.4 V	0.81	
				1.65 V	0.93	
				2.3 V	1.5	
Feed-through attenuation <sup>(3)</sup> (switch OFF)	COM or Y	Y or COM	$C_L = 50\text{ pF}$ , $R_L = 600\ \Omega$ , $f_{in} = 1\text{ MHz (sine wave)}$ (see Figure 9)	0.8 V	–60	dB
				1.1 V	–60	
				1.4 V	–60	
				1.65 V	–60	
				2.3 V	–60	
			$C_L = 5\text{ pF}$ , $R_L = 600\ \Omega$ , $f_{in} = 1\text{ MHz (sine wave)}$ (see Figure 9)	0.8 V	–59	
				1.1 V	–59	
				1.4 V	–59	
				1.65 V	–59	
				2.3 V	–59	

(1) Adjust  $f_{in}$  voltage to obtain 0 dBm at output. Increase  $f_{in}$  frequency until dB meter reads –3 dB.

(2) Adjust  $f_{in}$  voltage to obtain 0 dBm at input.

(3) Adjust  $f_{in}$  voltage to obtain 0 dBm at input.

**Analog Switch Characteristics (continued)** $T_A = 25^\circ\text{C}$ 

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	V <sub>CC</sub>	TYP	UNIT
Sine-wave distortion	COM or Y	Y or COM	$C_L = 50\text{ pF}$ , $R_L = 10\text{ k}\Omega$ , $f_{in} = 1\text{ kHz}$ (sine wave) (see Figure 10)	0.8 V	6.19	%
				1.1 V	0.39	
				1.4 V	0.06	
				1.65 V	0.02	
				2.3 V	0.01	
			$C_L = 50\text{ pF}$ , $R_L = 10\text{ k}\Omega$ , $f_{in} = 10\text{ kHz}$ (sine wave) (see Figure 10)	0.8 V	3.55	
				1.1 V	0.38	
				1.4 V	0.04	
				1.65 V	0.02	
				2.3 V	0.02	

**Operating Characteristics**for INH input,  $T_A = 25^\circ\text{C}$ 

PARAMETER	TEST CONDITIONS	V <sub>CC</sub> = 0.8 V	V <sub>CC</sub> = 1.2 V	V <sub>CC</sub> = 1.5 V	V <sub>CC</sub> = 1.8 V	V <sub>CC</sub> = 2.5 V	UNIT
		TYP	TYP	TYP	TYP	TYP	
$C_{pd}$ Power dissipation capacitance	f = 10 MHz	3	3	3	3	3	pF

**Operating Characteristics**for A input,  $T_A = 25^\circ\text{C}$ 

PARAMETER		TEST CONDITIONS	V <sub>CC</sub> = 0.8 V	V <sub>CC</sub> = 1.2 V	V <sub>CC</sub> = 1.5 V	V <sub>CC</sub> = 1.8 V	V <sub>CC</sub> = 2.5 V	UNIT
			TYP	TYP	TYP	TYP	TYP	
$C_{pd}$ Power dissipation capacitance	Outputs enabled	f = 10 MHz	5.5	5.5	5.5	5.5	5.5	pF
	Outputs disabled		0.5	0.5	0.5	0.5	0.5	

PARAMETER MEASUREMENT INFORMATION

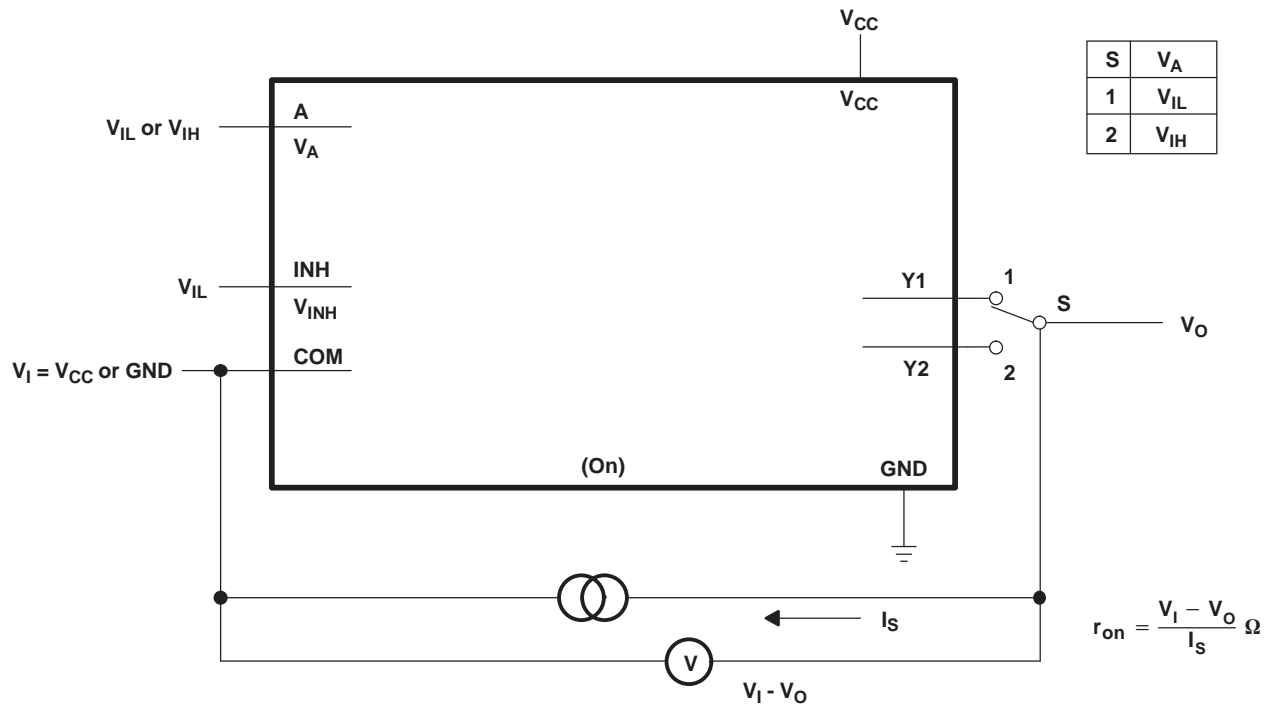


Figure 1. On-State Resistance Test Circuit

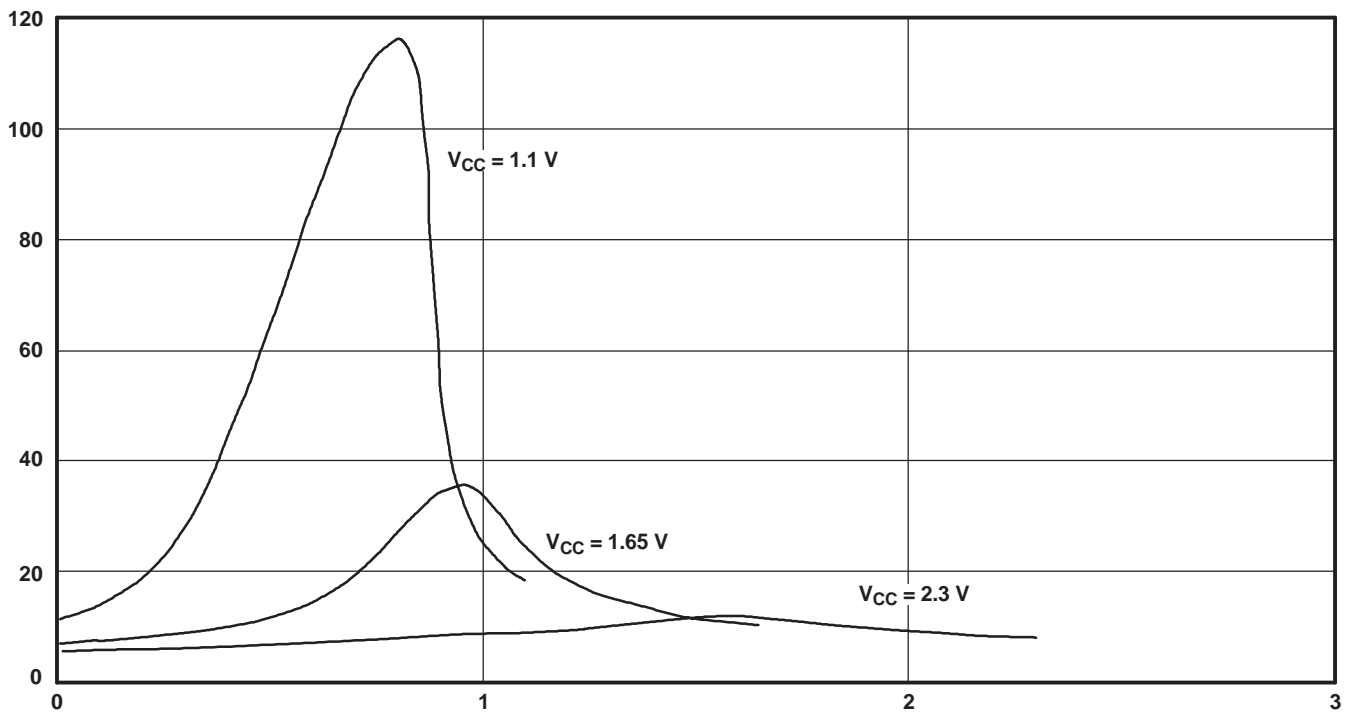


Figure 2. Typical  $r_{on}$  as a Function of Voltage ( $V_I$ ) for  $V_I = 0$  to  $V_{CC}$

PARAMETER MEASUREMENT INFORMATION

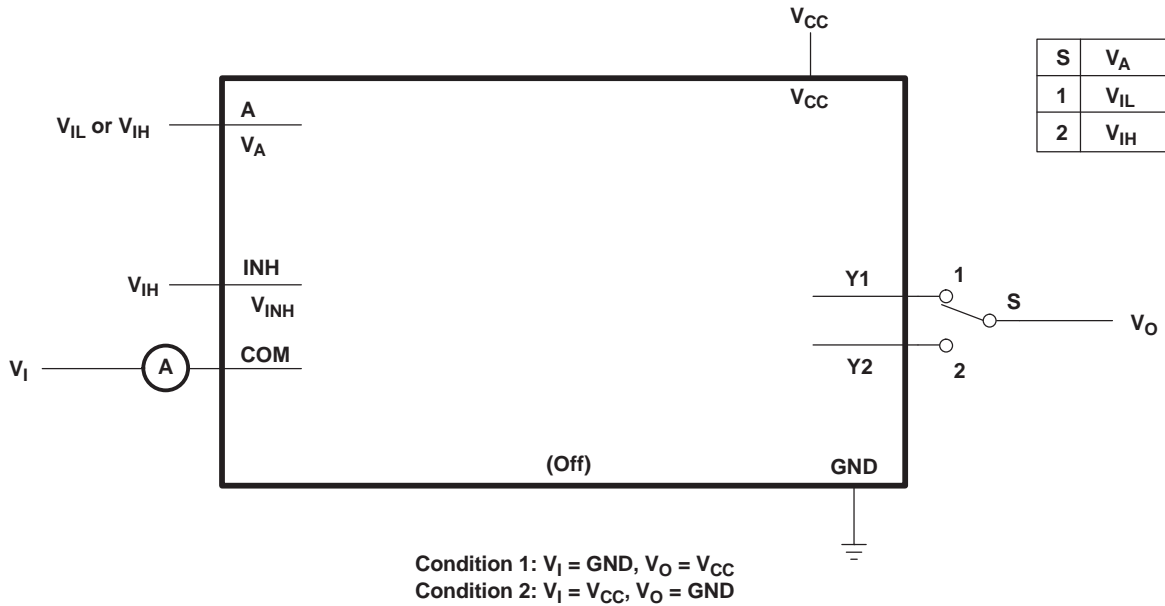


Figure 3. Off-State Switch Leakage-Current Test Circuit

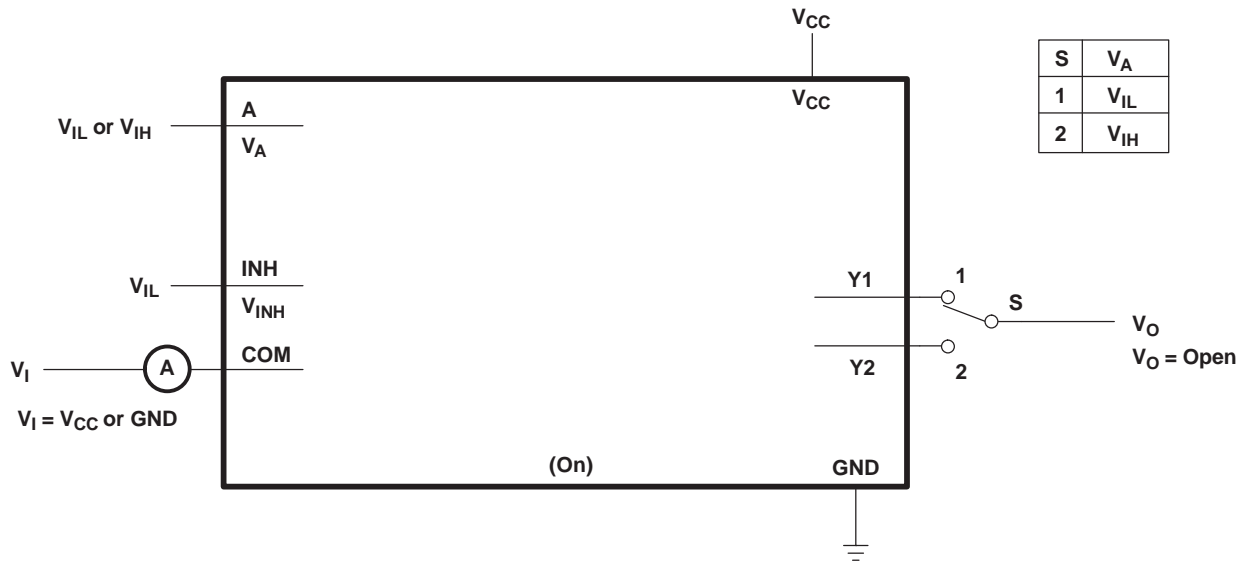
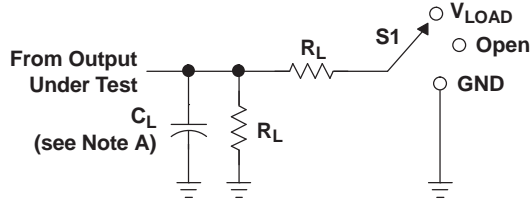


Figure 4. On-State Switch Leakage-Current Test Circuit



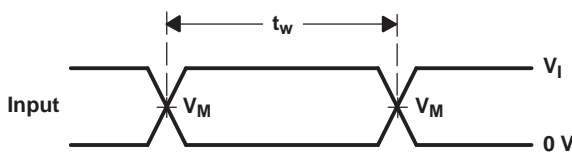
PARAMETER MEASUREMENT INFORMATION



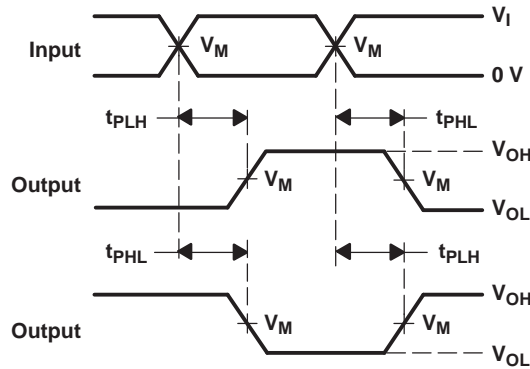
TEST	S1
$t_{PLH}/t_{PHL}$	Open
$t_{PLZ}/t_{PZL}$	$V_{LOAD}$
$t_{PHZ}/t_{PZH}$	GND

LOAD CIRCUIT

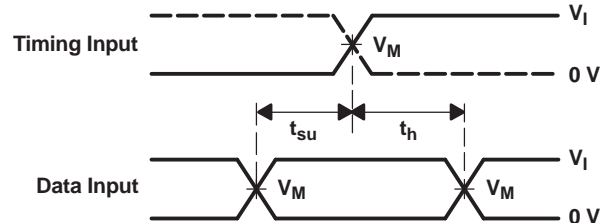
$V_{CC}$	INPUTS		$V_M$	$V_{LOAD}$	$C_L$	$R_L$	$V_{\Delta}$
	$V_I$	$t_r/t_f$					
0.8 V	$V_{CC}$	$\leq 2$ ns	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	2 k $\Omega$	0.1 V
$1.2 \text{ V} \pm 0.1 \text{ V}$	$V_{CC}$	$\leq 2$ ns	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	2 k $\Omega$	0.1 V
$1.5 \text{ V} \pm 0.1 \text{ V}$	$V_{CC}$	$\leq 2$ ns	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	2 k $\Omega$	0.1 V
$1.8 \text{ V} \pm 0.15 \text{ V}$	$V_{CC}$	$\leq 2$ ns	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	2 k $\Omega$	0.15 V
$2.5 \text{ V} \pm 0.2 \text{ V}$	$V_{CC}$	$\leq 2$ ns	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	2 k $\Omega$	0.15 V
$1.8 \text{ V} \pm 0.15 \text{ V}$	$V_{CC}$	$\leq 2$ ns	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	1 k $\Omega$	0.15 V
$2.5 \text{ V} \pm 0.2 \text{ V}$	$V_{CC}$	$\leq 2$ ns	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	500 $\Omega$	0.15 V



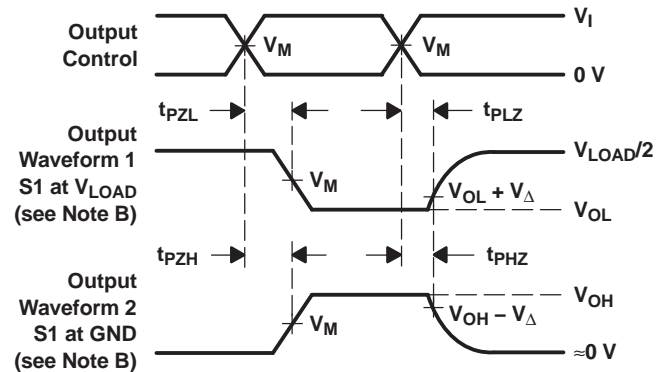
VOLTAGE WAVEFORMS PULSE DURATION



VOLTAGE WAVEFORMS PROPAGATION DELAY TIMES INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS ENABLE AND DISABLE TIMES LOW- AND HIGH-LEVEL ENABLING

- NOTES:
- A.  $C_L$  includes probe and jig capacitance.
  - B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
  - C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_O = 50 \Omega$ , slew rate  $\geq$  1 V/ns.
  - D. The outputs are measured one at a time, with one transition per measurement.
  - E.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .
  - F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .
  - G.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{pd}$ .
  - H. All parameters and waveforms are not applicable to all devices.

Figure 5. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION

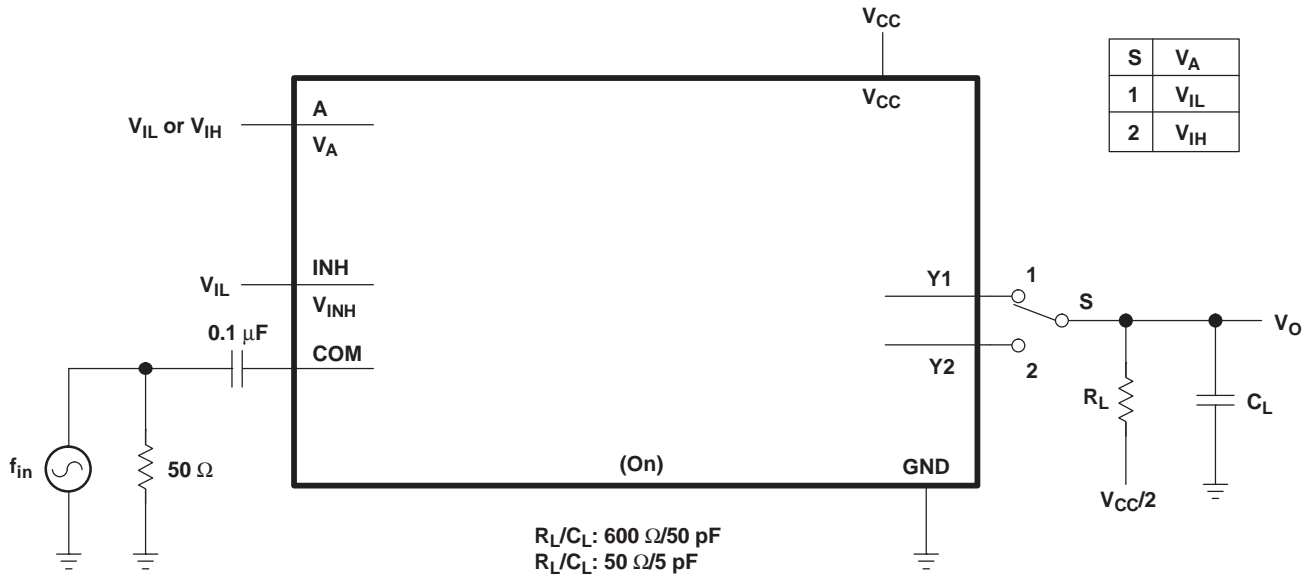


Figure 6. Frequency Response (Switch On)

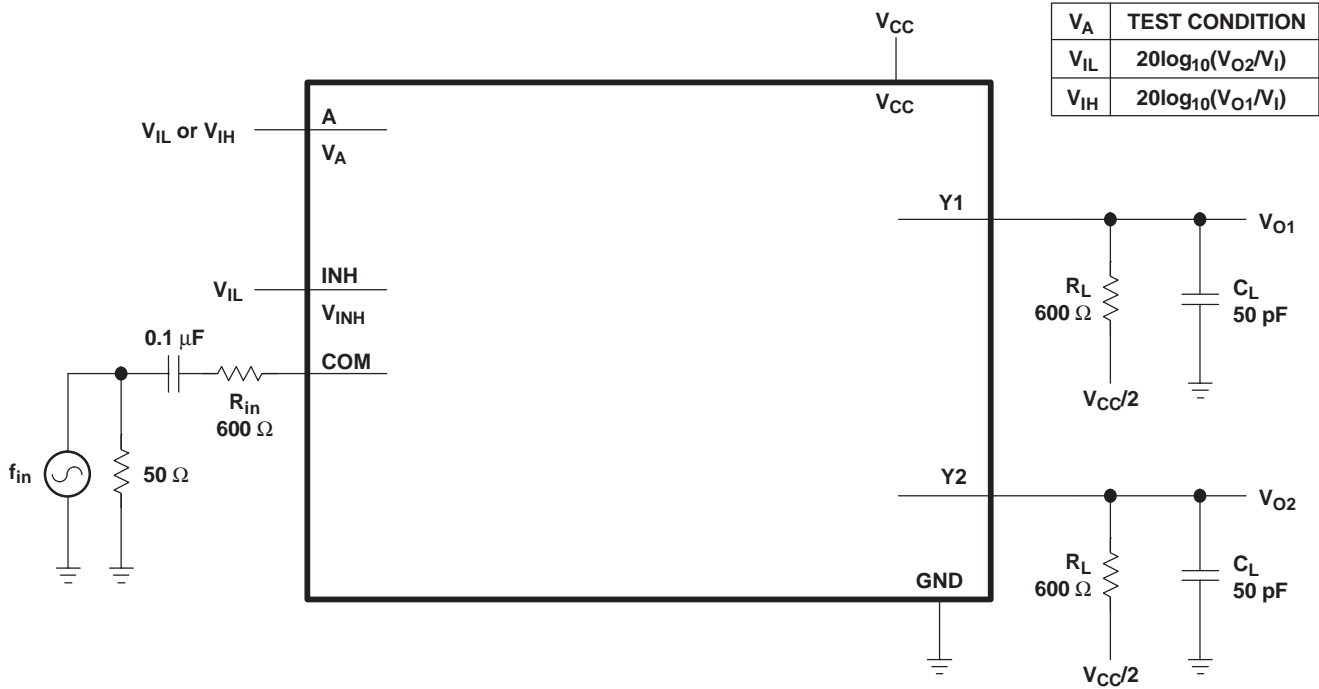


Figure 7. Crosstalk (Between Switches)

PARAMETER MEASUREMENT INFORMATION

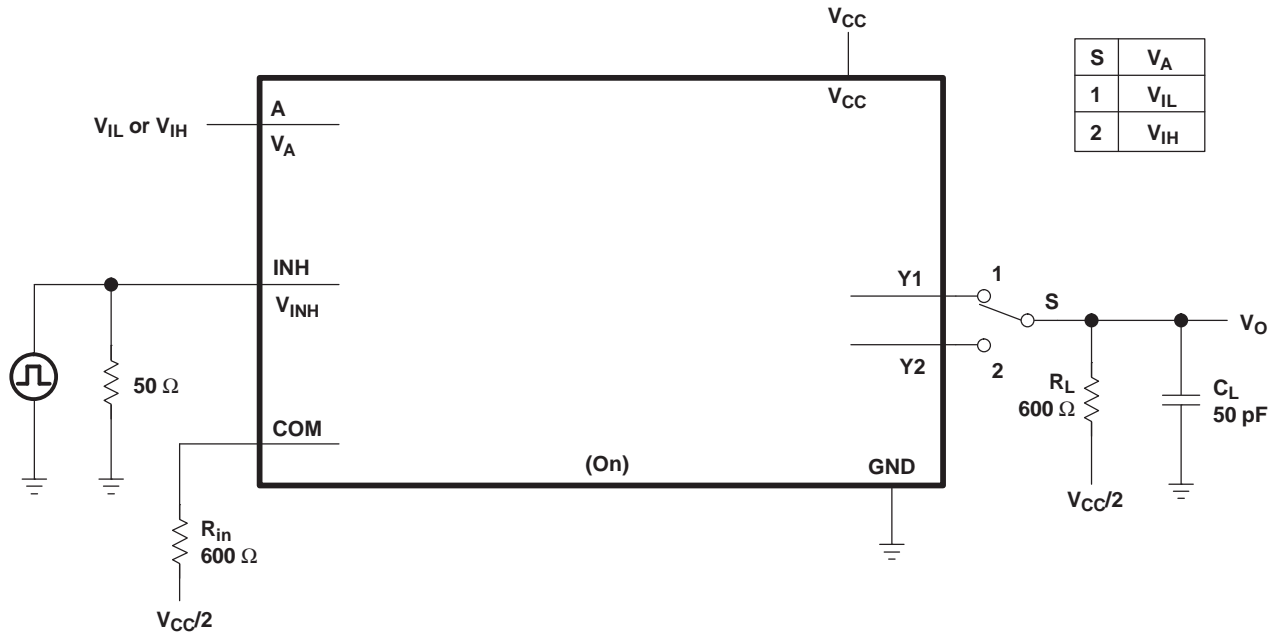


Figure 8. Crosstalk (Control Input, Switch Output)

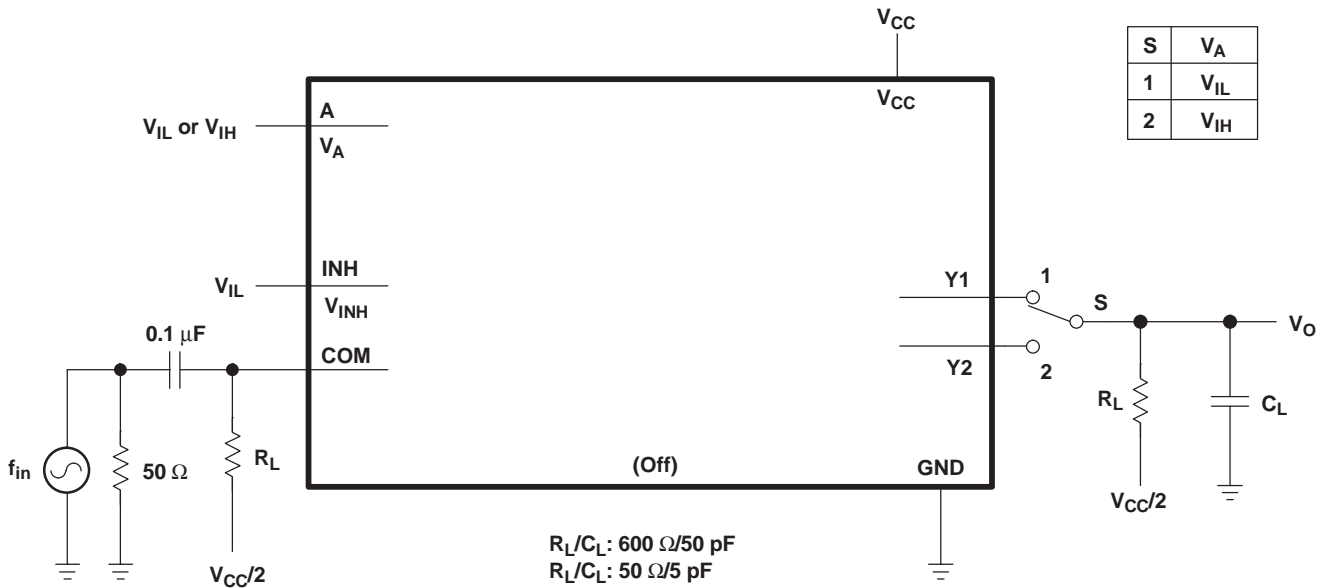


Figure 9. Feedthrough (Switch Off)

PARAMETER MEASUREMENT INFORMATION

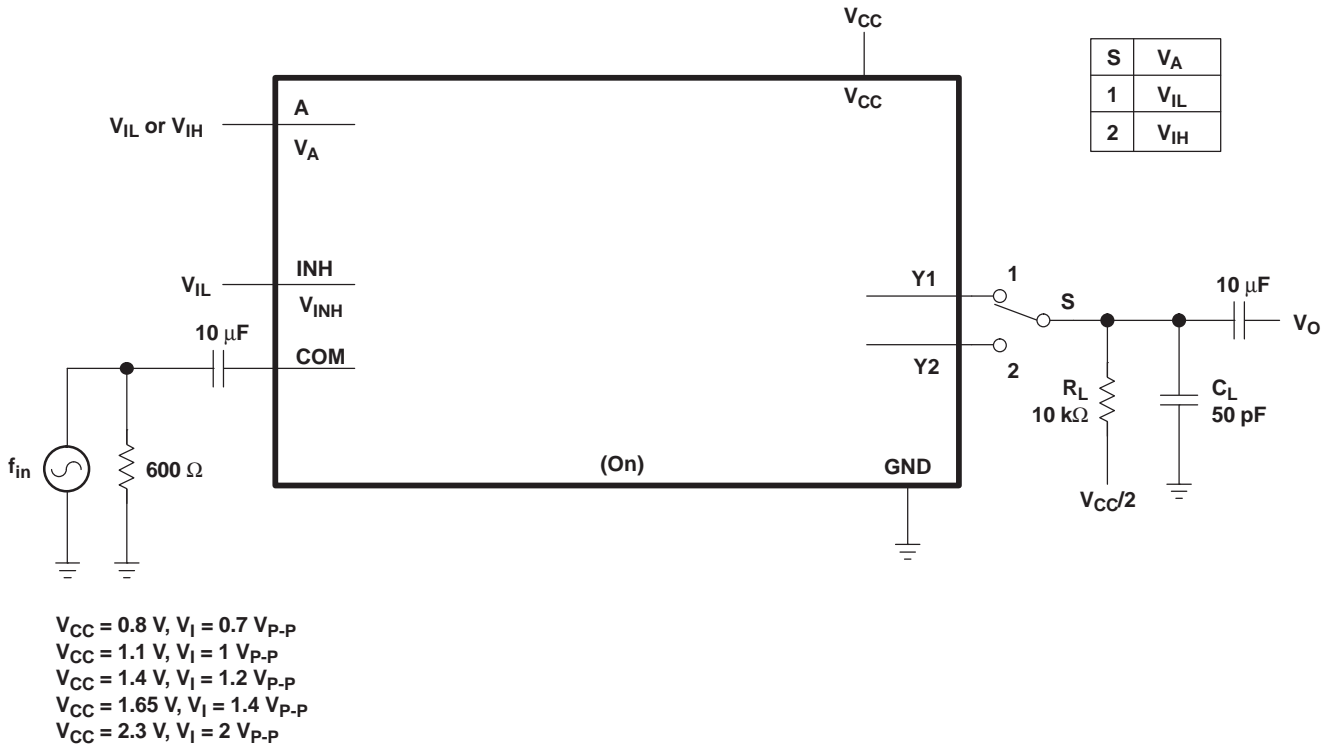


Figure 10. Sine-Wave Distortion

**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74AUC2G53DCTR	ACTIVE	SM8	DCT	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	U53 Z	<a href="#">Samples</a>
SN74AUC2G53DCTRE4	ACTIVE	SM8	DCT	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	U53 Z	<a href="#">Samples</a>
SN74AUC2G53DCUR	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-40 to 85	(U53Q, U53R)	<a href="#">Samples</a>
SN74AUC2G53DCURG4	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	U53R	<a href="#">Samples</a>
SN74AUC2G53YZPR	ACTIVE	DSBGA	YZP	8	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	U4N	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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## TAPE AND REEL INFORMATION



### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



\*All dimensions are nominal

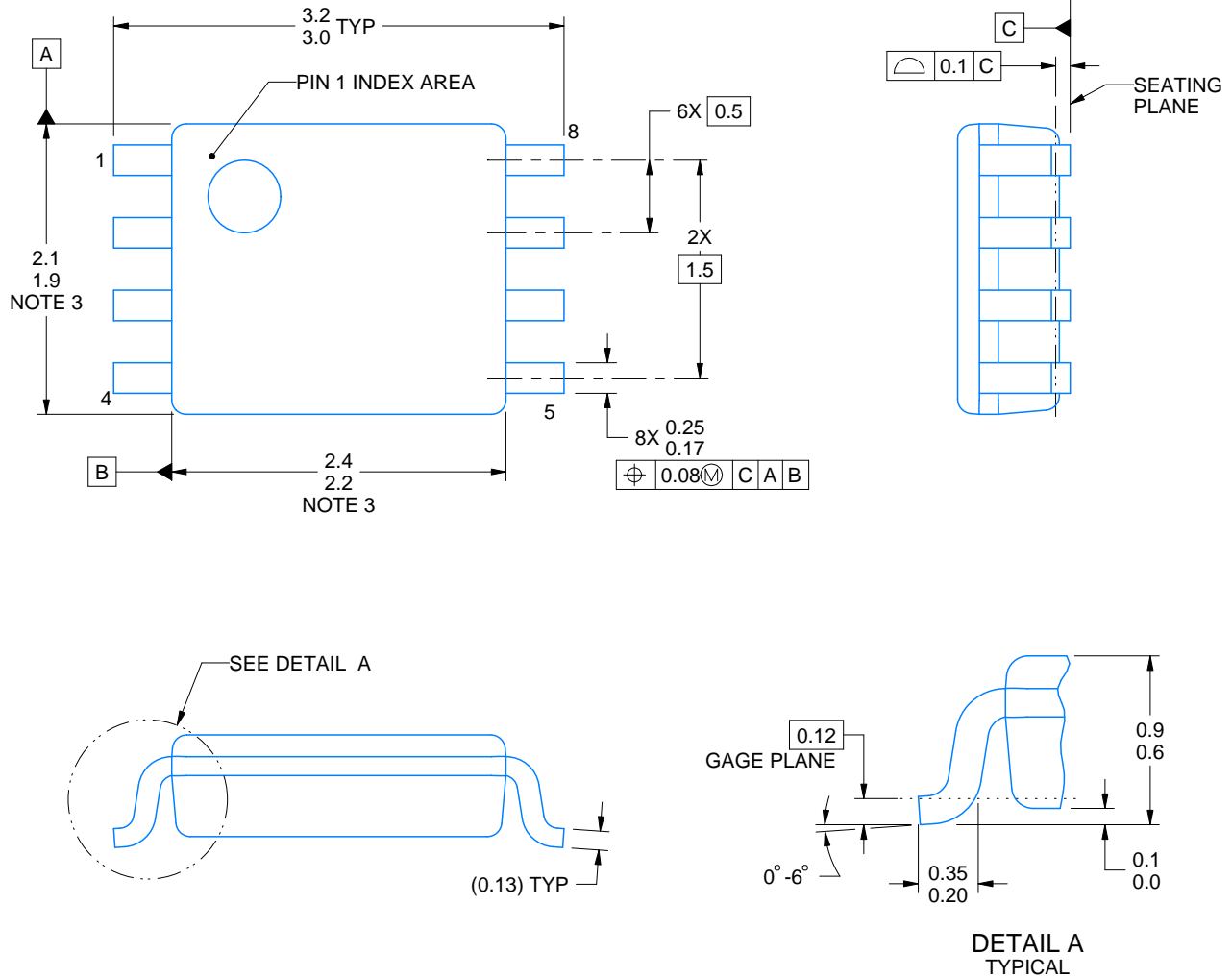
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74AUC2G53DCTR	SM8	DCT	8	3000	180.0	13.0	3.35	4.5	1.55	4.0	12.0	Q3
SN74AUC2G53DCUR	VSSOP	DCU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74AUC2G53DCURG4	VSSOP	DCU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74AUC2G53YZPR	DSBGA	YZP	8	3000	178.0	9.2	1.02	2.02	0.63	4.0	8.0	Q1

**TAPE AND REEL BOX DIMENSIONS**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74AUC2G53DCTR	SM8	DCT	8	3000	182.0	182.0	20.0
SN74AUC2G53DCUR	VSSOP	DCU	8	3000	202.0	201.0	28.0
SN74AUC2G53DCURG4	VSSOP	DCU	8	3000	202.0	201.0	28.0
SN74AUC2G53YZPR	DSBGA	YZP	8	3000	220.0	220.0	35.0





4225266/A 09/2014

NOTES:

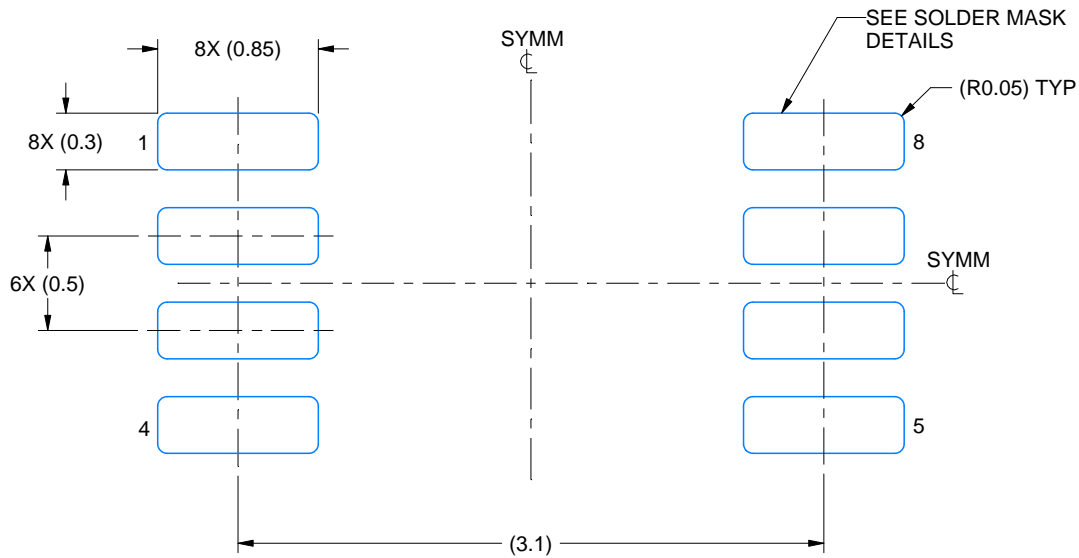
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. Reference JEDEC registration MO-187 variation CA.

# EXAMPLE BOARD LAYOUT

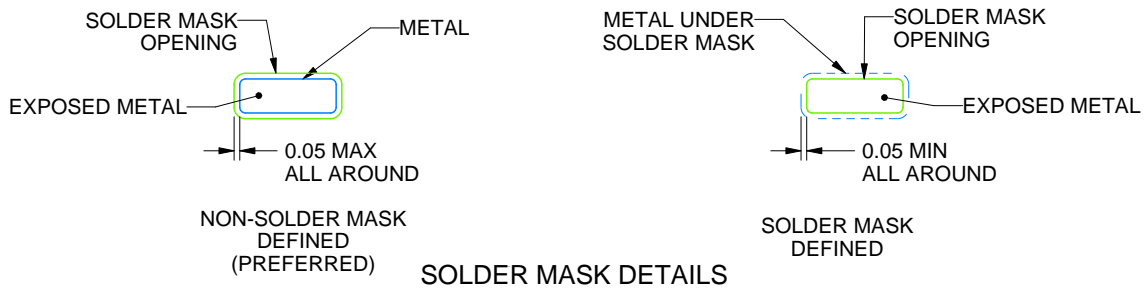
DCU0008A

VSSOP - 0.9 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE: 25X



4225266/A 09/2014

NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

# EXAMPLE STENCIL DESIGN

DCU0008A

VSSOP - 0.9 mm max height

SMALL OUTLINE PACKAGE

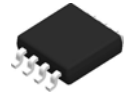


SOLDER PASTE EXAMPLE  
BASED ON 0.125 mm THICK STENCIL  
SCALE: 25X

4225266/A 09/2014

NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.



4220784/C 06/2021

NOTES:

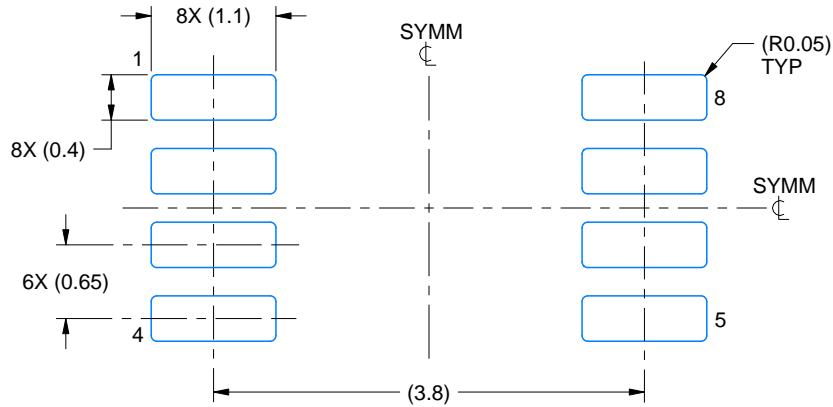
1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.

# EXAMPLE BOARD LAYOUT

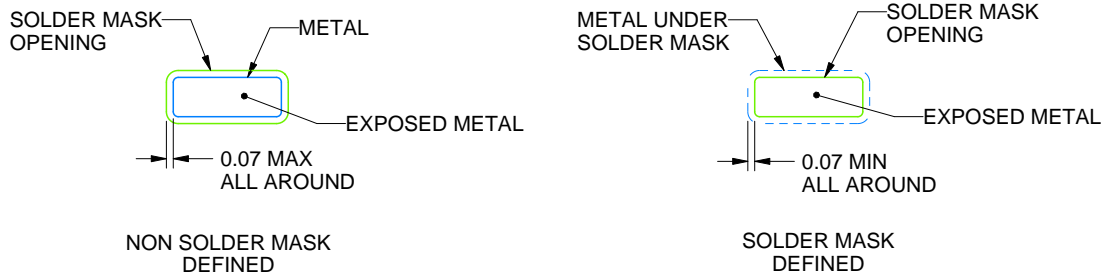
DCT0008A

SSOP - 1.3 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE:15X



SOLDER MASK DETAILS

4220784/C 06/2021

NOTES: (continued)

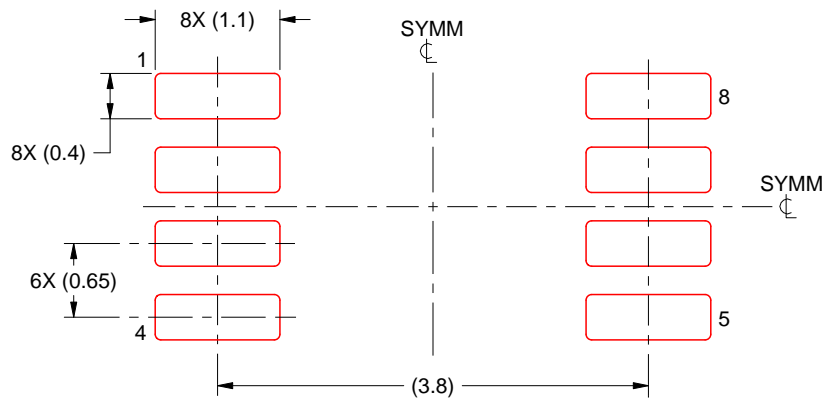
- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

# EXAMPLE STENCIL DESIGN

DCT0008A

SSOP - 1.3 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE  
BASED ON 0.125 mm THICK STENCIL  
SCALE:15X

4220784/C 06/2021

NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

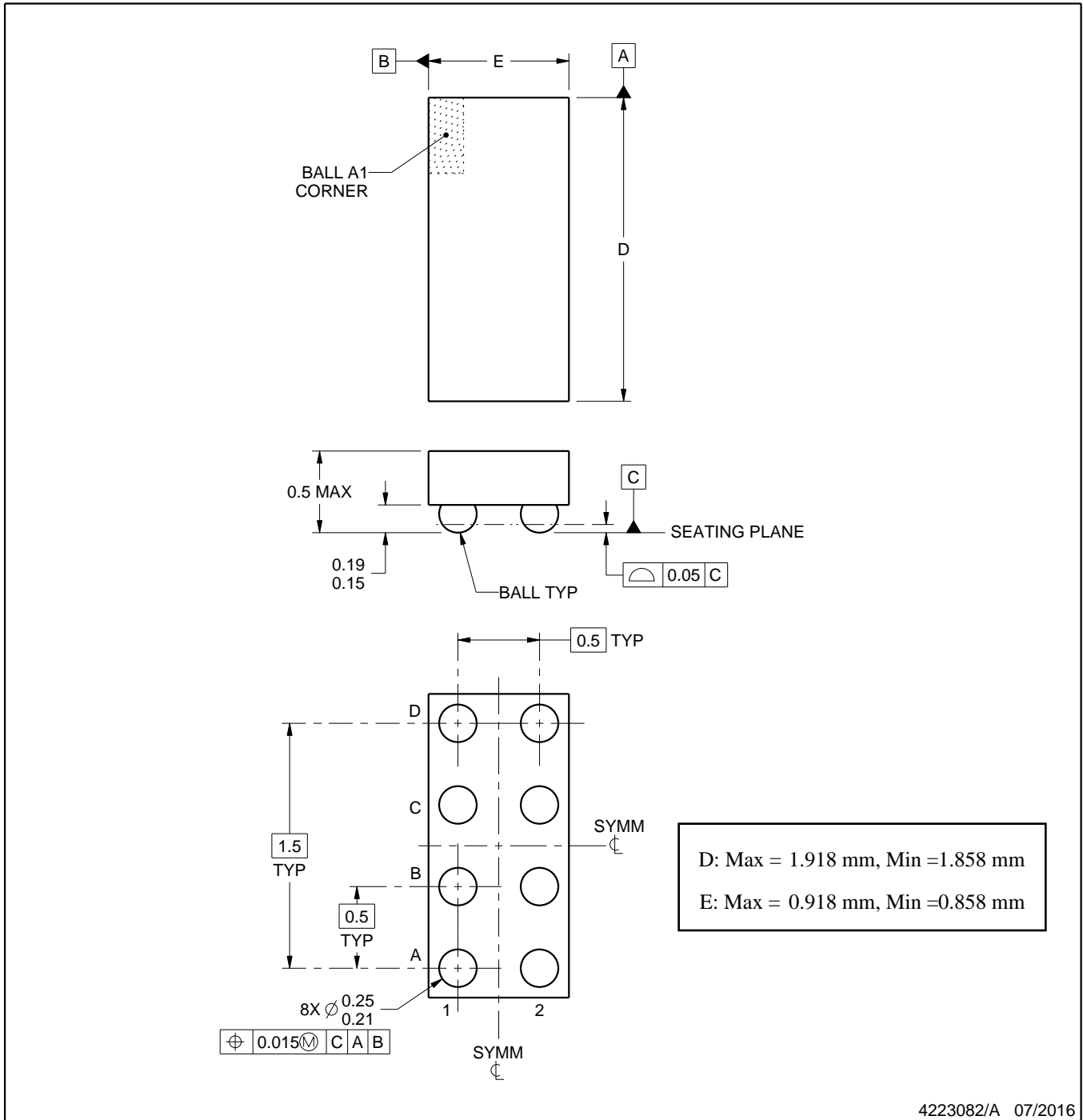
YZP0008



# PACKAGE OUTLINE

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



4223082/A 07/2016

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.

# EXAMPLE BOARD LAYOUT

YZP0008

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



LAND PATTERN EXAMPLE  
SCALE:40X



SOLDER MASK DETAILS  
NOT TO SCALE

4223082/A 07/2016

NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 ([www.ti.com/lit/snva009](http://www.ti.com/lit/snva009)).



# EXAMPLE STENCIL DESIGN

YZP0008

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



SOLDER PASTE EXAMPLE  
BASED ON 0.1 mm THICK STENCIL  
SCALE:40X

4223082/A 07/2016

NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

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